SCH1345

ON Semiconductor®

P-Channel Power MOSFET –20V, –4.5A, 49mΩ, Single SCH6

http://onsemi.com

Features

- On-resistance $R_{DS}(on)1=42m\Omega$ (typ)
- Halogen free compliance

- −1.5V drive
- Protection diode in

Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Value	Unit
Drain to Source Voltage	VDSS		-20	V
Gate to Source Voltage	V _{GSS}		±10	V
Drain Current (DC)	ID		-4.5	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	-18	Α
Power Dissipation	PD	When mounted on ceramic substrate(900mm ² ×0.8mm)	1	W
Junction Temperature	Tį		150	°C
Storage Temperature	Tstg		−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

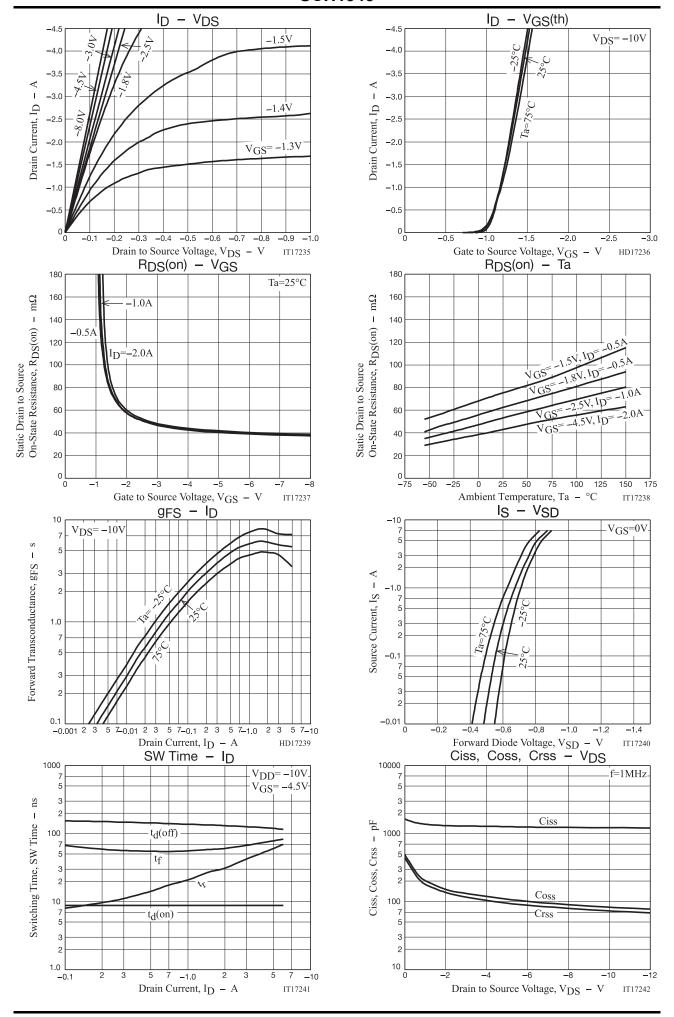
Electrical Characteristics at Ta = 25°C

Doromotor	Cymphol	Conditions	Value			1.1	
Parameter	Symbol	Conditions	min	typ	max	Unit	
Drain to Source Breakdown Voltage V(BR)DS		I _D =-1mA, V _{GS} =0V	-20			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =-20V, V _{GS} =0V			-1	μΑ	
Gate to Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±10	μΑ	
Gate Threshold Voltage	VGS(th)	V _{DS} =-10V, I _D =-1mA	-0.4		-1.3	V	
Forward Transconductance	gFS	V _{DS} =-10V, I _D =-2A		6		S	
	R _{DS} (on)1	I _D =-2A, V _G S=-4.5V		42	49	mΩ	
Static Drain to Source On-State Resistance	R _{DS} (on)2	I _D =-1A, V _G S=-2.5V		53	64	mΩ	
Static Drain to Source On-State Resistance	R _{DS} (on)3	I _D =-0.5A, V _G S=-1.8V		65	85	mΩ	
	R _{DS} (on)4	I _D =-0.5A, V _G S=-1.5V		74	120	mΩ	
Input Capacitance	Ciss			1220		pF	
Output Capacitance	Coss	V _{DS} =-10V, f=1MHz		82		pF	
Reverse Transfer Capacitance	Crss			72		pF	
Turn-ON Delay Time	t _d (on)			8.8		ns	
Rise Time	t _r	Constitution of Constitution		35		ns	
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		123		ns	
Fall Time	tf			61		ns	
Total Gate Charge	Qg			11		nC	
Gate to Source Charge	Qgs	V _{DS} =-10V, V _{GS} =-4.5V, I _D =-4.5A		1.9		nC	
Gate to Drain "Miller" Charge	Qgd			1.9		nC	
Forward Diode Voltage	V _{SD}	I _S =-4.5A, V _{GS} =0V		-0.82	-1.2	V	

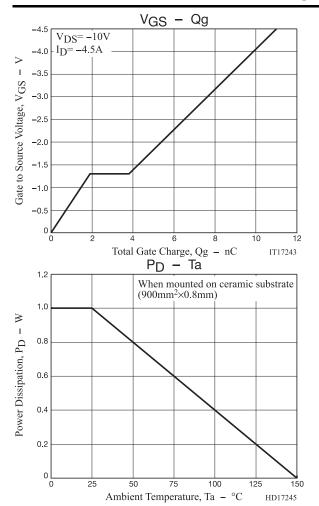
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

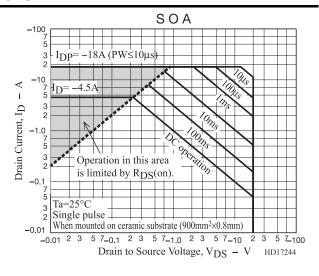
ORDERING INFORMATION

See detailed ordering and shipping information on page 4 of this data sheet.



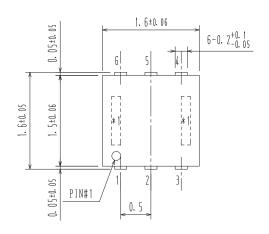
SCH1345

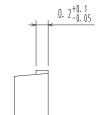




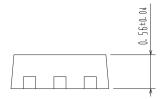
Package Dimensions

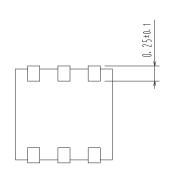
SCH1345-TL-H unit:mm SOT-563 / SCH6 CASE 463AB ISSUE O



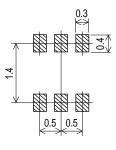


- 1 : Drain
- 2 : Drain
- 3 : Gate
- 4 : Source
- 5 : Drain
- 6: Drain





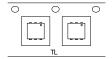
Recommended Soldering Footprint



Ordering & Package Information

_	_		
Device	Package	Shipping	note
SCH1345-TL-H	SCH6 SOT-563	5,000 pcs. / reel	Pb-Free And Halogen Free

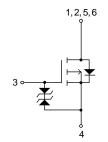
Packing Type: TL



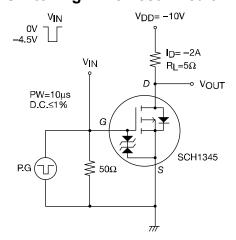
Marking



Electrical Connection



Switching Time Test Circuit



Note on usage: Since the SCH1345 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

ON Semiconductor and the ON logo are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equa